WHAT IS CLAIMED IS:

1. A gettering layer forming method for forming a gettering layer on a back side of a wafer having devices formed on a front side, the gettering layer forming method comprising:

a coating step of dropping a solution of metal salt from a nozzle onto the back side of the wafer while rotating the wafer; and

a drying step of drying the wafer after performing the coating step, thereby forming the gettering layer containing the metal salt on the back side of the wafer;

wherein the gettering layer is not removed from the back side of the wafer after the drying step, and is provided on the back side of each of the devices to prevent reduction of die strength of each device.

2. The gettering layer forming method according to claim 1, wherein the metal salt contains divalent metal, and the gettering layer contains 1×10^{13} atoms or more of the divalent metal per cm^2.

3. The gettering layer forming method according to claim 1, wherein the metal salt contains trivalent metal, and the gettering layer contains 1×10^{12} atoms or more of the trivalent metal per cm^2.